1. General description

PNP high-voltage low V_{CEsat} Breakthrough Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-140	V
I _C	collector current		-	-	-4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	100	150	mΩ



140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. M
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PBHV9414Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9414Z	V9414Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-180	V
V _{CEO}	collector-emitter voltage	open base		-	-140	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-10	Α
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			<u>[2]</u>	-	1	W
			[<u>3]</u>	-	1.35	W
T _j	junction temperature			-	150	°C

PBHV9414Z

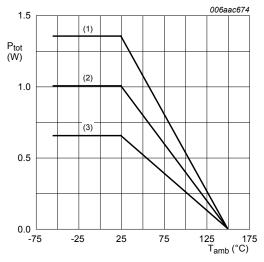
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140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Max	Unit
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig a)	thermal resistance	in free air	[1]	-	-	192	K/W
	from junction to		[2]	-	-	125	K/W
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

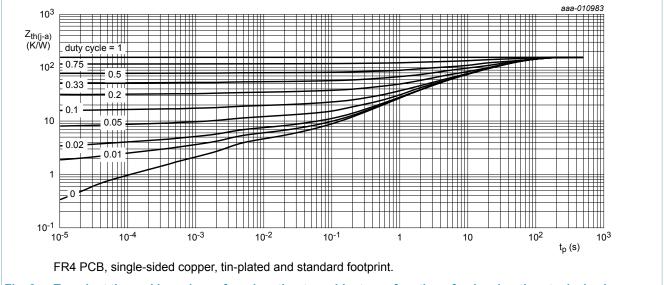
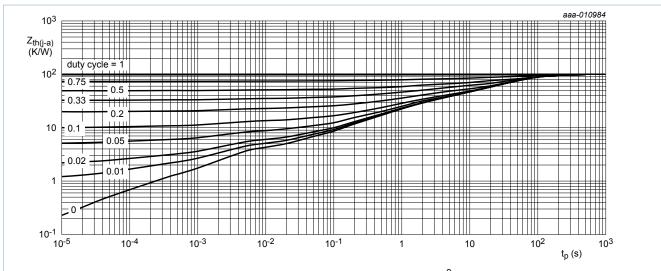


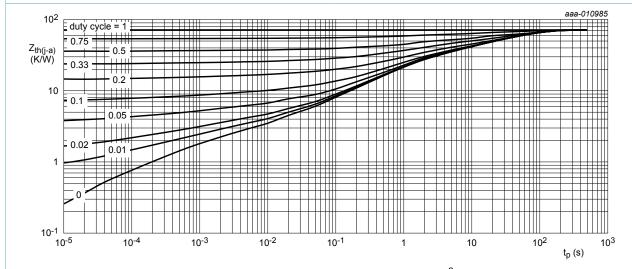
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm²

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

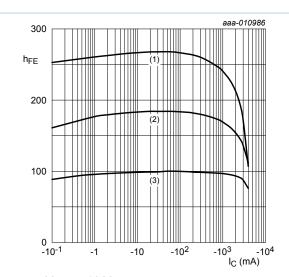
140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -150 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -150 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μΑ
CES	collector-emitter cut-off current	V _{CE} = -115 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
ЕВО	emitter-base cut-off current	V _{EB} = -6 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
1 _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -10 mA; T_{amb} = 25 °C	100	160	-	
		V_{CE} = -5 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	100	150	300	
		V_{CE} = -5 V; I_{C} = -3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	75	100	-	
		V_{CE} = -5 V; I_{C} = -4 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	35	50	-	
	collector-emitter saturation voltage	I_{C} = -100 mA; I_{B} = -5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-45	-60	mV
		I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-60	-100	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-100	-150	mV
		I_{C} = -3 A; I_{B} = -300 mA; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; T_{amb} = 25 °C; pulsed	-	-275	-370	mV
		I_{C} = -4 A; I_{B} = -400 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-420	-550	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	100	150	mΩ
/ _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-1.2	V
/ _{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	-	-1.1	V

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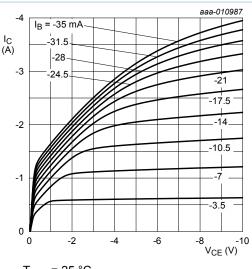
$$V_{CE} = -10 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

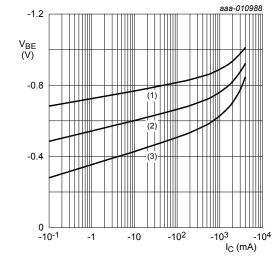
(3)
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



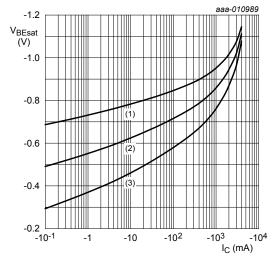
$$V_{CE} = -10 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

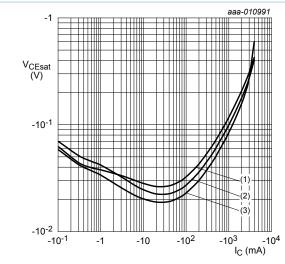
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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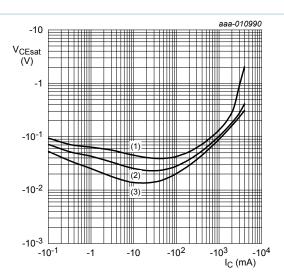
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



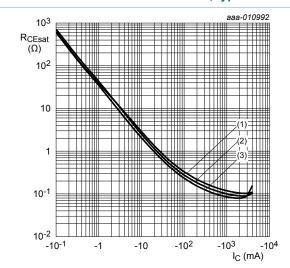
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



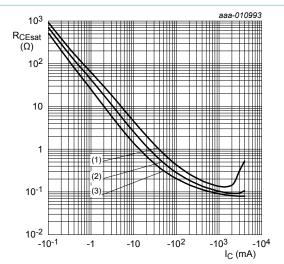
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55$$
 °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

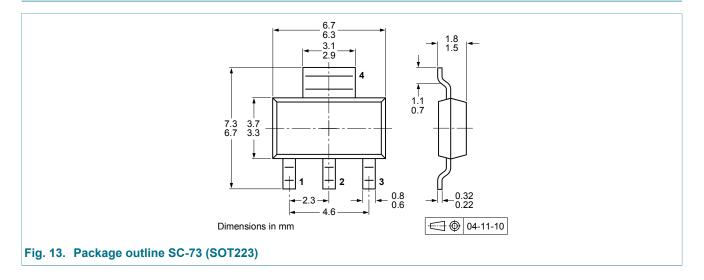
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11. Test information

11.1 Quality information

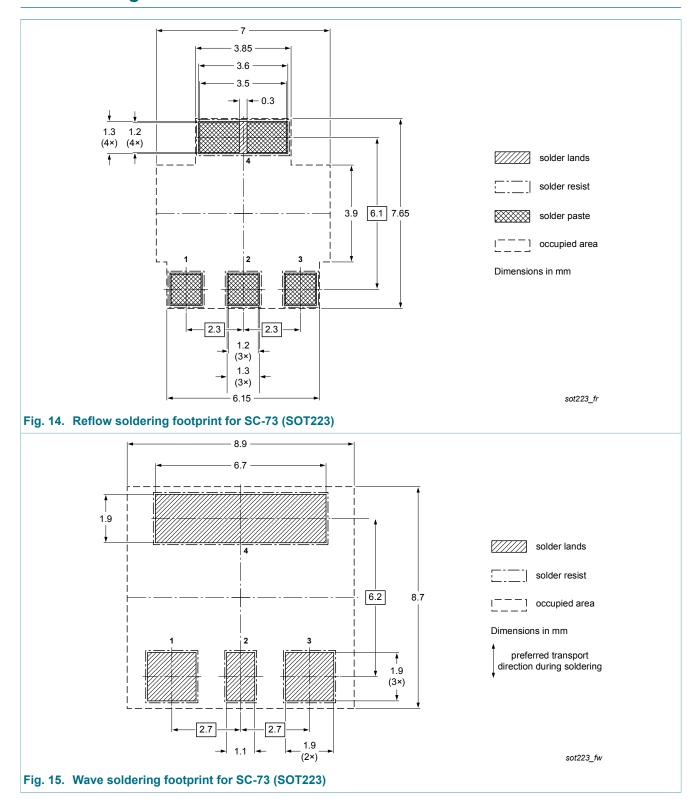
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



140 V, 4 A PNP high-voltage low VCEsat (BISS) transistor

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBHV9414Z v.2	20140124	Product data sheet	-	PBHV9414Z v.1		
Modifications:	Product status changed					
PBHV9414Z v.1	20131001	Objective data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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